80 V NPN, 10 A Power Transistor

These series of plastic, silicon NPN power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Fast Switching Speeds
- High Frequency
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

Applications

- High-end Consumer Audio Products
 - Home Amplifiers
 - Home Receivers

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	10	Α
Collector Current - Peak (Note 1)	I _{CM}	20	Α
Total Power Dissipation @ T _C = 25°C	P _D	120	Watts

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.04	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



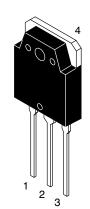
ON Semiconductor®

http://onsemi.com

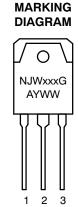
80 VOLT, 10 AMPS NPN POWER TRANSISTORS

NPN COLLECTOR 2, 4

EMITTER 3



TO-3P PLASTIC CASE 340AB



xxx = TBD

G = Pb-Free Package

A = Assembly Location

Y = Year WW = Work Week

ORDERING INFORMATION

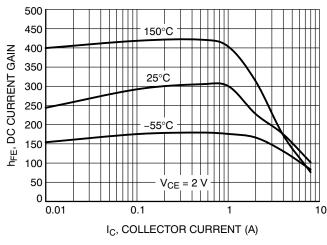
Device	Package	Shipping
NJW44H11G	TO-3P (Pb-Free)	30 Units/Rail

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•
Collector–Emitter Sustaining Voltage ($I_C = 30 \text{ mAdc}, I_B = 0$)	V _{CEO}	80	-	-	Vdc
Collector–Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{BE} = 0)$	I _{CES}	-	-	10	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc)	I _{EBO}	-	-	10	μAdc
ON CHARACTERISTICS					•
DC Current Gain $ (I_C = 2 \text{ A, } V_{CE} = 2 \text{ V}) $ $ (I_C = 4 \text{ A, } V_{CE} = 2 \text{ V}) $	h _{FE}	100 80	- -	400 320	-
Collector–Emitter Saturation Voltage (I _C = 8 A, I _B = 400 mA)	V _{CE(sat)}	-	-	1.0	V
Base-Emitter Turn-on Voltage (I _C = 8 A, V _{CE} = 2.0 V)	V _{BE(on)}	-	_	1.5	V
DYNAMIC CHARACTERISTICS	•				•
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	65	_	pF
Cutoff Frequency (I _C = 500 mA, V _{CE} = 5 V, f = 1.0 MHz)	f⊤	-	85	-	MHz
SWITCHING TIMES	•		!		
Delay and Rise Times (I _C = 5.0 Adc, I _{B1} = 0.5 A)	$t_d + t_r$	-	300	-	ns
Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t _s	-	500	-	ns
Fall Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t _f	-	140	-	ns

TYPICAL CHARACTERISTICS

500



450 150°C 400 hFE, DC CURRENT GAIN 350 25°C 300 250 200 150 100 50 0 0.01 10 I_C, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain

Figure 2. DC Current Gain

150°

10

25°C

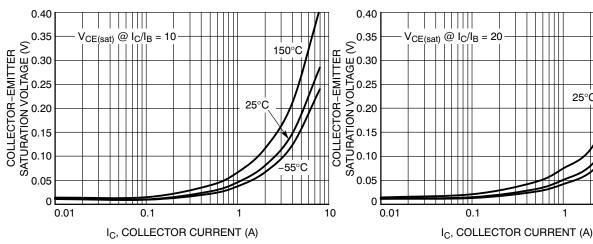
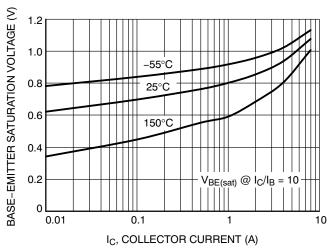


Figure 3. Collector Emitter Saturation Voltage

Figure 4. Collector Emitter Saturation Voltage



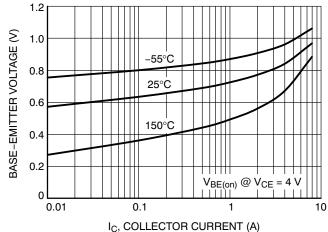
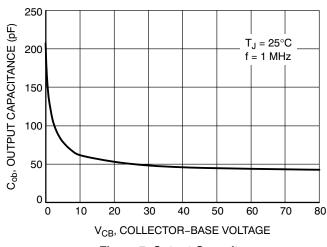


Figure 5. Base Emitter Saturation Voltage

Figure 6. Base Emitter "ON" Voltage

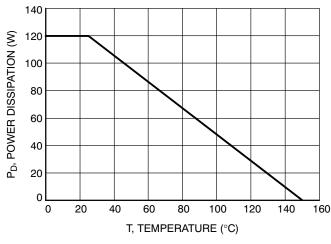
TYPICAL CHARACTERISTICS



HLONG SO TO TO THE STATE OF THE

Figure 7. Output Capacitance

Figure 8. Current Gain Bandwidth Product



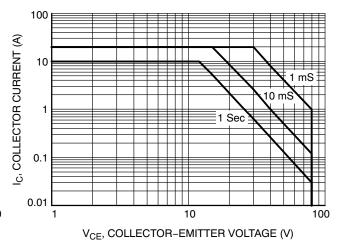
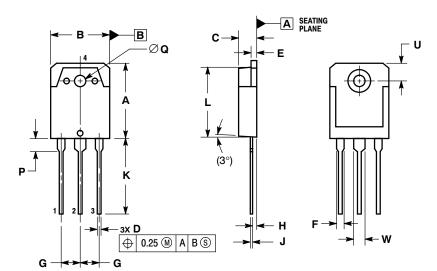


Figure 9. Power Temperature Derating

Figure 10. Safe Operating Area (SOA)

PACKAGE DIMENSIONS

TO-3P-3LD CASE 340AB-01 ISSUE A



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
 DIMENSION & APPLIES TO PLATED TERMINAL
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- 4. DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	19.70	19.90	20.10	
В	15.40	15.60	15.80	
С	4.60	4.80	5.00	
D	0.80	1.00	1.20	
E	1.45	1.50	1.65	
F	1.80	2.00	2.20	
G	5.45 BSC			
Н	1.20	1.40	1.60	
J	0.55	0.60	0.75	
K	19.80	20.00	20.20	
L	18.50	18.70	18.90	
P	3.30	3.50	3.70	
Q	3.10	3.20	3.50	
U	5.00 REF			
W	2.80	3.00	3.20	

STYLE 1:

PIN 1. BASE

2. COLLECTOR

EMITTER
 COLLECTOR

STYLE 2:

PIN 1. ANODE 2. CATHODE 3. ANODE

CATHODE

STYLE 3: PIN 1. GATE

2. DRAIN 3. SOURCE 4. DRAIN

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative